



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

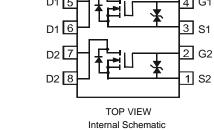
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2KV
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.072 grams (approximate)







TOP VIEW

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 3)	Steady State	$T_A = 25$ °C $T_A = 85$ °C	I _D	9.5 7.1	Α
Pulsed Drain Current (Note 4)		I _{DM}	30	Α	

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P_{D}	1.28	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 3)	R _{θJA}	99.3	°C/W
Operating and Storage Temperature Range	T _{.I} , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 4. Repetitive rating, pulse width limited by junction temperature.

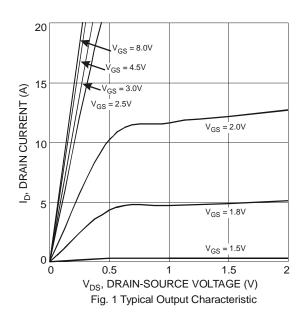


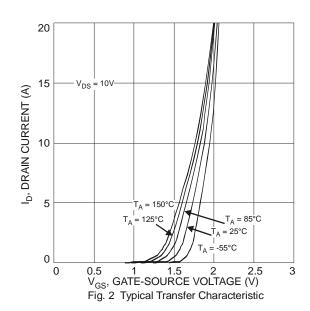
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	1	-	1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	1	-	±10	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(th)}$	0.5	1.0	1.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D		11	16 23	mΩ	$V_{GS} = 4.5V, I_D = 9.4A$	
Static Dialii-Source Off-Nesistance	R _{DS (ON)}	-	17			$V_{GS} = 2.5V, I_D = 8.3A$	
Forward Transfer Admittance	Y _{fs}	ı	17	1	S	$V_{DS} = 5V, I_{D} = 9.4A$	
Diode Forward Voltage	V _{SD}	1	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1.3A$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	C _{iss}	ı	1149	1	pF	101/1/	
Output Capacitance	Coss	ı	157	1	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	ı	142	-	рF	1 = 1.0MH2	
Gate Resistance	R_{g}	1	1.51	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_{g}	ı	11.6	1	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	ı	26	1	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 9.4A$	
Gate-Source Charge	Q_{gs}	1	2.7	-	nC		
Gate-Drain Charge	Q_{gd}	-	3.4	-	nC		
Turn-On Delay Time	$t_{D(on)}$	-	11.67	-	ns	V_{DD} = 10V, V_{GS} = 4.5V, R_{GEN} = 6 Ω , I_{D} = 1A	
Turn-On Rise Time	t _r	-	12.49	-	ns		
Turn-Off Delay Time	t _{D(off)}	-	35.89	-	ns		
Turn-Off Fall Time	t _f	i	12.33	-	ns		

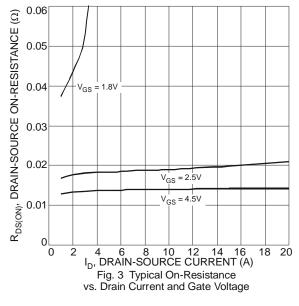
Notes:

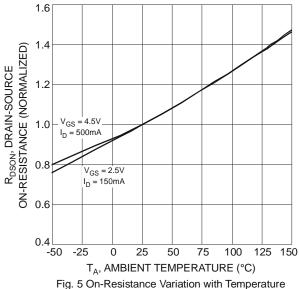
- 5. Short duration pulse test used to minimize self-heating effect.
- 6. Guaranteed by design. Not subject to production testing.











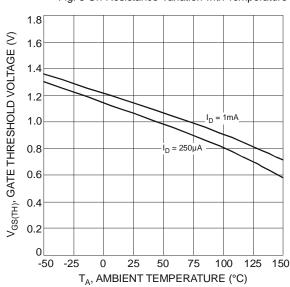
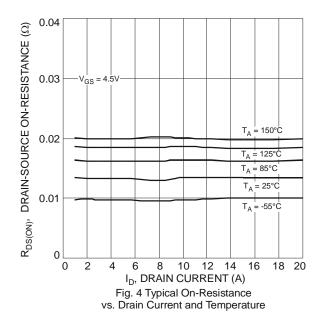


Fig. 7 Gate Threshold Variation vs. Ambient Temperature



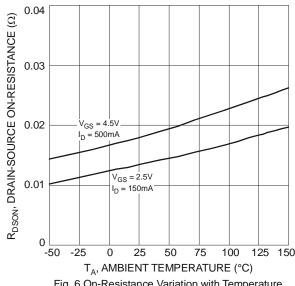


Fig. 6 On-Resistance Variation with Temperature

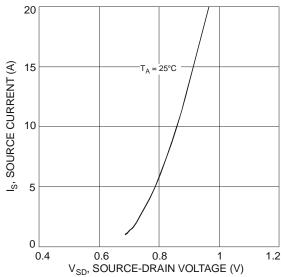
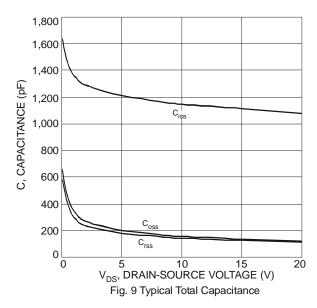
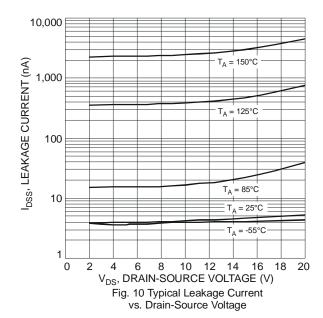
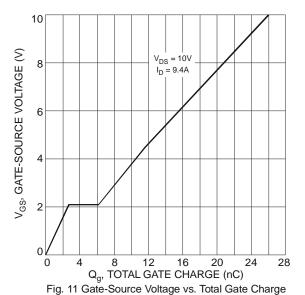


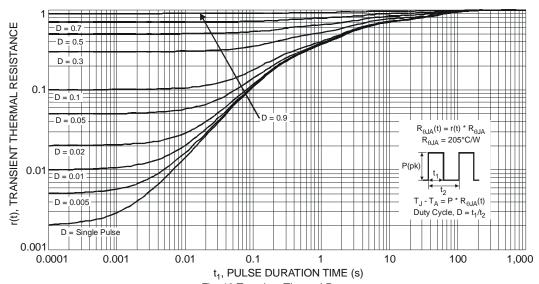
Fig. 8 Diode Forward Voltage vs. Current











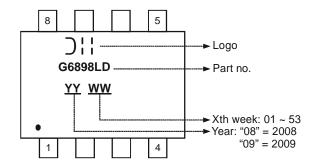


Ordering Information (Note 7)

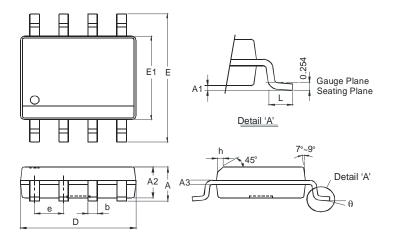
Part Number	Case	Packaging
DMG6898LSD-13	SO-8	2500 / Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

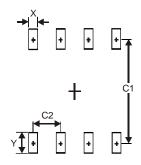


Package Outline Dimensions



SO-8				
Dim	Min	Max		
Α	-	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
А3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	e 1.27 Typ			
h	-	0.35		
٦	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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